

## UNISONIC TECHNOLOGIES CO., LTD

DBC2315 Preliminary DUAL TRANSISTOR

# DIGITAL TRANSISTOR (BUILT-IN BIAS RESISTORS)

### DESCRIPTION

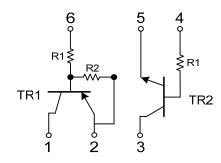
- \* Both the DTB123Y chip and DTC115T chip in a SOT-26 package.
- \* NPN/PNP silicon transistor(Built-in resistor type)

### **■ FEATURES**

- \* Built-in bias resistors that implies easy ON/OFF applications.
- \* The bias resistors are thin-film resistors with complete isolation to allow positive input.

# 6 5 4 3 3 1 2 SOT-26

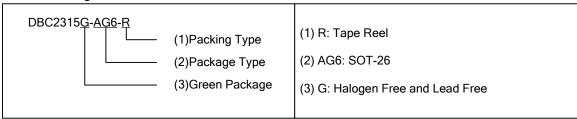
### **■** EQUIVALENT CIRCUITS



### **■ ORDERING INFORMATION**

Ordering Number	Package	Pin Assignment						Dooking	
		1	2	3	4	5	6	Packing	
DBC2315G-AG6-R	SOT-26	C1	E1	C2	B2	E2	B1	Tape Reel	

Note: Pin Assignment: C: Collector B: Bas E: Emitter



### **■** MARKING



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### ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	LIMITS	UNIT
Collector-Base Voltage	TR1	V <sub>CBO</sub>	-50	V
	TR2		50	V
Collector-Emitter Voltage	TR1	- V <sub>CEO</sub> -	-50	V
	TR2		50	V
Emitter-Base Voltage	TR1	V <sub>EBO</sub>	-5	V
	TR2		5	V
Collector Current	TR1	Ic	-500	mA
	TR2		100	mA
Collector Power Dissipation		Pc	200	mW
Junction Temperature		$T_J$	150	°C
Storage Temperature		T <sub>STG</sub>	-55~+150	ů

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

### ■ **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub>=25°C, unless otherwise specified)

### TR1 (PNP)

11(1)(1)(1)		-						
PARAMETER	SYMBOL	TEST CONDITIONS MIN		TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Input Voltage	V <sub>IN(OFF)</sub>	V <sub>CC</sub> =-5V, I <sub>OUT</sub> =-100μA			-0.3	V		
	V <sub>IN(ON)</sub>	V <sub>OUT</sub> =-0.3V, I <sub>OUT</sub> =-20mA	-2			V		
Output Voltage	V <sub>OUT(ON)</sub>	$I_{OUT}/I_{IN}$ =-50mA/-2.5mA		-0.1	-0.3	V		
Input Current	I <sub>IN</sub>	V <sub>IN</sub> =-5V			-3.0	mA		
Output Current	I <sub>OUT(OFF)</sub>	V <sub>CC</sub> =-50V, V <sub>IN</sub> =0V			-0.5	μA		
ON CHARACTERISTICS								
DC Current Gain	h <sub>FE</sub>	V <sub>OUT</sub> =-5V, I <sub>OUT</sub> =-50mA	56					
SMALL SIGNAL CHARACTERISTICS								
Input Resistance	R <sub>1</sub>		1.54	2.2	2.86	ΚΩ		
Resistor Ratio	R <sub>2</sub> /R <sub>1</sub>		3.6	4.5	5.5			
Transition Frequency (Note)	$f_T$	V <sub>CE</sub> =-10V, I <sub>E</sub> =50mA, f=100MHz		200		MHz		

### TR2 (NPN)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
OFF CHARACTERISTICS								
BV <sub>CBO</sub>	I <sub>C</sub> =50μA	50			V			
$BV_CEO$	I <sub>C</sub> =1mA	50			V			
$BV_{EBO}$	I <sub>E</sub> =50μA	5			V			
I <sub>CBO</sub>	V <sub>CB</sub> =50V			0.5	μΑ			
I <sub>EBO</sub>	V <sub>EB</sub> =4V			0.5	μΑ			
V <sub>CE(SAT)</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0.1mA			0.3	V			
ON CHARACTERISTICS								
h <sub>FE</sub>	$V_{CE}$ =5V, $I_{C}$ =1mA	100	250	600				
SMALL SIGNAL CHARACTERISTICS								
R1		70	100	130	ΚΩ			
f <sub>T</sub>	$V_{CE}$ =10V, $I_{E}$ =-5mA, f=100MHz		250		$MH_Z$			
	BV <sub>CBO</sub> BV <sub>CEO</sub> BV <sub>EBO</sub> I <sub>CBO</sub> I <sub>CBO</sub> I <sub>CE(SAT)</sub>	BV <sub>CBO</sub> I <sub>C</sub> =50μA BV <sub>CEO</sub> I <sub>C</sub> =1mA BV <sub>EBO</sub> I <sub>E</sub> =50μA I <sub>CBO</sub> V <sub>CB</sub> =50V I <sub>EBO</sub> V <sub>EB</sub> =4V V <sub>CE(SAT)</sub> I <sub>C</sub> =1mA, I <sub>B</sub> =0.1mA h <sub>FE</sub> V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	BV <sub>CBO</sub> I <sub>C</sub> =50μA     50       BV <sub>CEO</sub> I <sub>C</sub> =1mA     50       BV <sub>EBO</sub> I <sub>E</sub> =50μA     5       I <sub>CBO</sub> V <sub>CB</sub> =50V       I <sub>EBO</sub> V <sub>EB</sub> =4V       V <sub>CE(SAT)</sub> I <sub>C</sub> =1mA, I <sub>B</sub> =0.1mA       h <sub>FE</sub> V <sub>CE</sub> =5V, I <sub>C</sub> =1mA     100       R1     70	BV <sub>CBO</sub> I <sub>C</sub> =50μA     50       BV <sub>CEO</sub> I <sub>C</sub> =1mA     50       BV <sub>EBO</sub> I <sub>E</sub> =50μA     5       I <sub>CBO</sub> V <sub>CB</sub> =50V     0       I <sub>EBO</sub> V <sub>EB</sub> =4V     0       V <sub>CE(SAT)</sub> I <sub>C</sub> =1mA, I <sub>B</sub> =0.1mA     100     250       R1     70     100	BV <sub>CBO</sub> I <sub>C</sub> =50μA         50           BV <sub>CEO</sub> I <sub>C</sub> =1mA         50           BV <sub>EBO</sub> I <sub>E</sub> =50μA         5           I <sub>CBO</sub> V <sub>CB</sub> =50V         0.5           I <sub>EBO</sub> V <sub>EB</sub> =4V         0.5           V <sub>CE(SAT)</sub> I <sub>C</sub> =1mA, I <sub>B</sub> =0.1mA         0.3           h <sub>FE</sub> V <sub>CE</sub> =5V, I <sub>C</sub> =1mA         100         250         600           R1         70         100         130			

Note: Transition frequency of the device.

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